

Notice of References Cited

Application/Control No.
09/522,707

Applicant(s)/Patent Under Reexam
Hiramatsu et al.

Examiner
B. William Baumeister

Art Unit
2815
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U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
A	6,153,010	11/2000	Kiyoku et al.	117	95
B	6,325,850	12/2001	Beaumont et al.	117	95
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E	6,051,849	4/2000	Davis et al.	257	103
F	5,874,747	2/1999	Redwing et al.	257	77
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N					
O					
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NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages	
U	Nakamura et al., "Long lifetime violet InGaN/GaNAIGaN-based semiconductor lasers," 5/28/1998, pp. 52-58.	
V	Yu, et al., "Study of the epitaxial-lateral-overgrowth (ELOO process for GaN on sapphire," Journal of Crystal Growth 195 (1998) 333-339.	
W	Sakai et al., "Defect structure in selectively grown GaN films with low threading dislocation density," Appl. Phys. Lett. 71 (1-6) 20 October 1997, pp. 2259-2261.	
X	Wong et al., "Damage-free separation of GaN thin films from sapphire substrates," Appl. Phys. Lett. 72 (5), 2 February 1998, pp. 599-601.	

¹ A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

¹ Dates in MM-YYYY format are publication dates.

² Classifications may be U.S. or foreign.

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U	Jones et al., "Characteristics of GaN Stripes Grown by Selective-Area Metalorganic Chemical Vapor Deposition," Journal of Electronic Materials, Vol. 26, No. 3, 1997, pp. 306-310.		
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